

# **NCE N-Channel Super Trench II Power MOSFET**

#### **Description**

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

## **Application**

- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

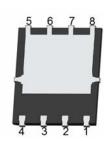
#### **General Features**

- $V_{DS}$  =120V, $I_D$  =57A  $R_{DS(ON)}$ =9.5m $\Omega$  , typical@  $V_{GS}$ =10V  $R_{DS(ON)}$ =12.5m $\Omega$  , typical@  $V_{GS}$ =4.5V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 150 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

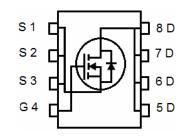
#### **DFN 5X6**





**Top View** 

**Bottom View** 



**Schematic Diagram** 

### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P11N12AGU	NCEP11N12AGU	DFN5X6-8L	-	-	=

#### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	120	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	57	А
Drain Current-Continuous(T <sub>C</sub> =100℃)	I <sub>D</sub> (100℃)	40	Α
Pulsed Drain Current	I <sub>DM</sub>	228	Α
Maximum Power Dissipation	P <sub>D</sub>	85	W
Derating factor		0.68	W/℃
Single pulse avalanche energy (Note 4)	E <sub>AS</sub>	260	mJ
Operating Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 To 150	$^{\circ}$

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	1.47	°C/W
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Electrical Characteristics (T<sub>C</sub>=25 °C unless otherwise noted)

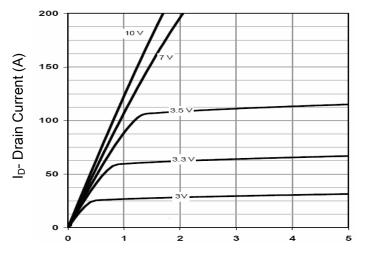
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	120		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =120V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}$ = $V_{GS}$ , $I_D$ =250 $\mu$ A	1.1	1.7	2.5	V
Drain-Source On-State Resistance	В	$V_{GS}$ =10V, $I_{D}$ =28.5A	-	9.5	11	mΩ
Dialii-Source Oil-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =4.5V, $I_D$ =28.5A	-	12.5	15	11122
Gate resistance	R <sub>G</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1.0MHz	-	2.5	-	Ω
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =28.5A		50	-	S
Dynamic Characteristics (Note3)						
Input Capacitance	C <sub>lss</sub>	V -00V/V -0V	-	2800	-	pF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =60V, $V_{GS}$ =0V, F=1.0MHz		180	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			20	-	pF
Switching Characteristics (Note 3)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	13	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =60V, $I_{D}$ =28.5A	-	10	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{G}$ =1.6 $\Omega$	-	30	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8	-	nS
Total Gate Charge	Qg	\/ -E0\/  -20.EA	-	56	-	nC
Gate-Source Charge	Qgs	$V_{DS}$ =50V, $I_{D}$ =28.5A,	-	12.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V		14	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 2)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =28.5A	-	-	1.2	V
Diode Forward Current	Is		-	-	57	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C, I_F = 28.5A$	-	55	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	98	-	nC

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 3. Guaranteed by design, not subject to production
- 4. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V  $_{DD}$  =50 V,V  $_{G}$  =10 V,L=0.25 mH,Rg=25  $\Omega$

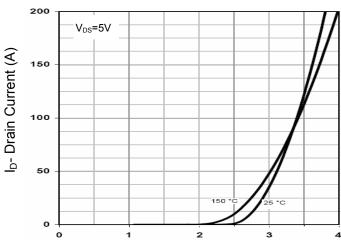


## **Typical Electrical and Thermal Characteristics**



Vds Drain-Source Voltage (V)





Vgs Gate-Source Voltage (V)
Figure 2 Transfer Characteristics

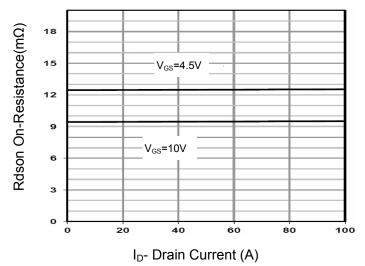
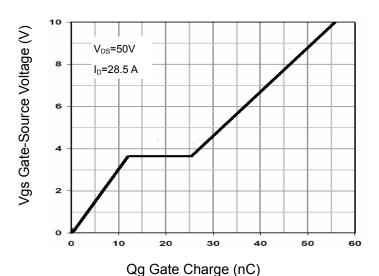


Figure 3 Rdson- Drain Current



**Figure 4 Gate Charge** 

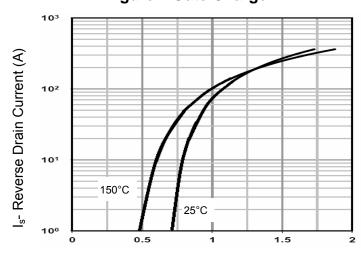
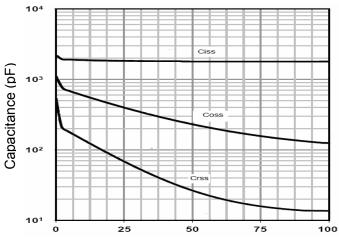


Figure 5 Source- Drain Diode Forward

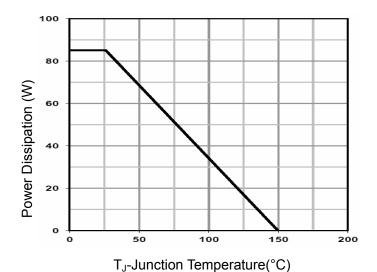
Vsd Source-Drain Voltage (V)



Vds Drain-Source Voltage (V)

Figure 6 Capacitance vs Vds

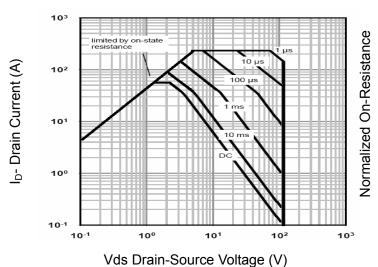




100

Figure 7 Power De-rating

T<sub>J</sub>-Junction Temperature (°C) **Figure 9 Current De-rating** 



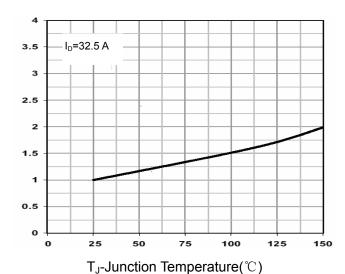


Figure 8 Safe Operation Area

**Figure 10 Rdson-Junction Temperature** 

V2.0

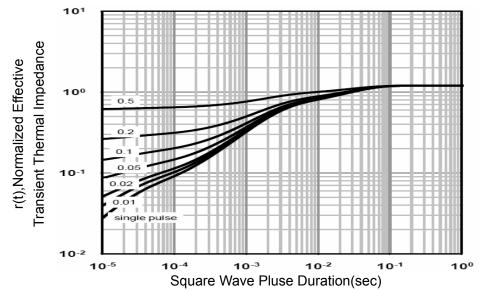
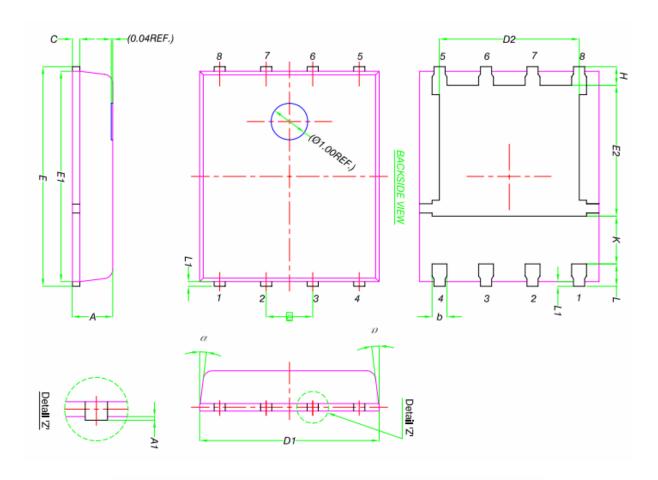


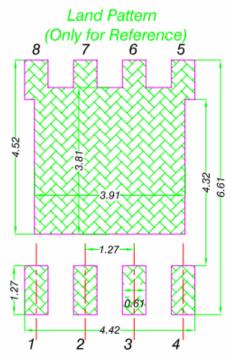
Figure 11 Normalized Maximum Transient Thermal Impedance



# **DFN5X6-8L Package Information**



	MILLIMETERS				
DIM.	MIN.	NOM.	MAX.		
Α	0.90	1.00	1.10		
A1	0	-	0.05		
b	0.33	0.41	0.51		
С	0.20	0.25	0.30		
D1	4.80	4.90	5.00		
D2	3.61	3.81	3.96		
Ε	5.90	6.00	6.10		
E1	5.70	5.75	5.80		
E2	3.38	3.58	3.78		
е					
Н	H 0.41		0.61		
К	1.10	-	-		
L	L 0.51 L1 0.06		0.71 0.20		
L1					
α	0°	-	12°		





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